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Dr. Md. Nur Kutubul Alam
Associate Professor
Research Area Solid state Electronic Devices

Biography

Md. Nur Kutubul Alam is serving as a lecturer at Khulna University of Engineering and Technology (KUET). He received his BSc in Electrical and Electronic Engineering from KUET with Honors in 2012, and pursuing his MSc in the same university. He is the only son of late Md. Abdur Rafique and Kaniz Fatema. His father was an Electrical engineer who was a proud employee of Bangladesh Power Development Board (BPDB) throughout his life.

Currently, Md. Nur Kutubul Alam is working on Solid State Electronic Devices. His ongoing research is on modeling and simulation of low-dimensional devices for ultra low power logic application.

Education

Research Interest

Solid state Electronic Devices
III-V Semiconductors for ultra-fast active devices
III-V Semiconductors on insulator for low-power high-speed devices
Suitable device design for long distance high speed communication hardware

Publication

Books

Journals

4. , " Researchgate," ***(Which is the social network of researchers)***

4. Nur,M. , Alam,K. , Islam,M. S. , Kibria,G. and Islam,M. R. (2014) , " Anomalous Staircase CV Characteristics of InGaSb-on-Insulator FET," ***IEEE Transaction on Electron Devices***

2. Pinky,L. J. R. , Islam,S. , Alam,M. N. K. , Hossain,M. A. and Islam,M. R. (2014) , " Modeling of Orientation-Dependent Photoelastic Constants in Cubic Crystal System," ***Materials Sciences and Applications***, Scientific Research , vol5, no.4, pp.223-230

1. Islam,M. S. ,Alam,M. N. K. and Islam,M. R. (2013) , " InxGa1-xSb n-channel MOSFET: Effect of interface states on CV characteristics," ***International Journal of Nanotechnology***, Inderscience Publishers, volForthcoming articles

Conference

7. Islam,M. S. ,Alam,M. N. K. and Islam,M. R. (24 May 2014) , "Effect of gate length on the ballistic performance of nanoscale InGaSb double gate MOSFET," ***2014 International Conference on Informatics, Electronics & Vision (ICIEV)*** , IEEE, pp.1-4

6. Alam,M. N. K. ,Islam,M. S. and Islam,M. R. (5/6/2013) , "Self-consistent quasi-static C-V characteristics of In1âˆ’xGaxSb XOI FET," ***EDSSC-2013*** , IEEE, pp.2

5. Alam,M. N. K. ,Islam,M. S. and Islam,M. R. (5/6/2013) , "Capacitance-Voltage characterization of InAsySb1âˆ’y XOI FET," ***EDSSC-2013*** , IEEE, pp.2

3. Islam,M. S. ,Alam,M. N. K. and Islam,M. R. , "Self-Consistent Quasi Static CV Characterization of InxGa1-xSb Buried Channel n-MOSFET," ***IEEE International Nanoelectronics Conference***

2. Islam,M. S. , Nayeem,M. O. G. , Alam,M. N. K. and Islam,M. R. , "InGaSb based n-MOSFET: Modeling and Performance Analysis," ***International Conference on Electrical and Computer Engineering (ICECE)***

1. Alam,M. N. K. , Nayeem,M. O. G. , Islam,M. S. and Islam,M. R. , "Ultra High-Current-Gain InxGa1-xSb-based DHBT With Compositional Graded Base," ***International Conference on Electrical and Computer Engineering (ICECE)***